

DUAL OP AMP AND VOLTAGE REFERENCE

AP4310/A

Pin Configuration

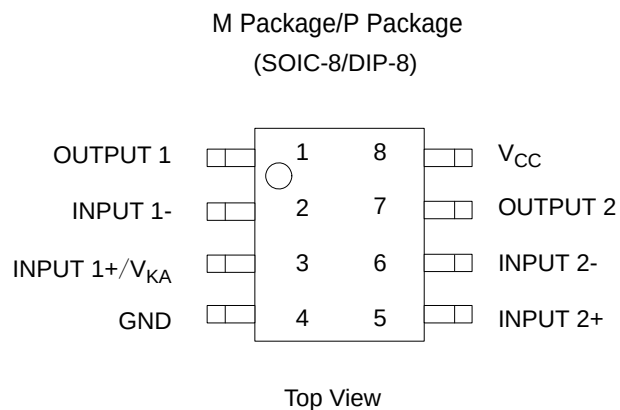


Figure 2. Pin Configuration of AP4310/A

Functional Block Diagram

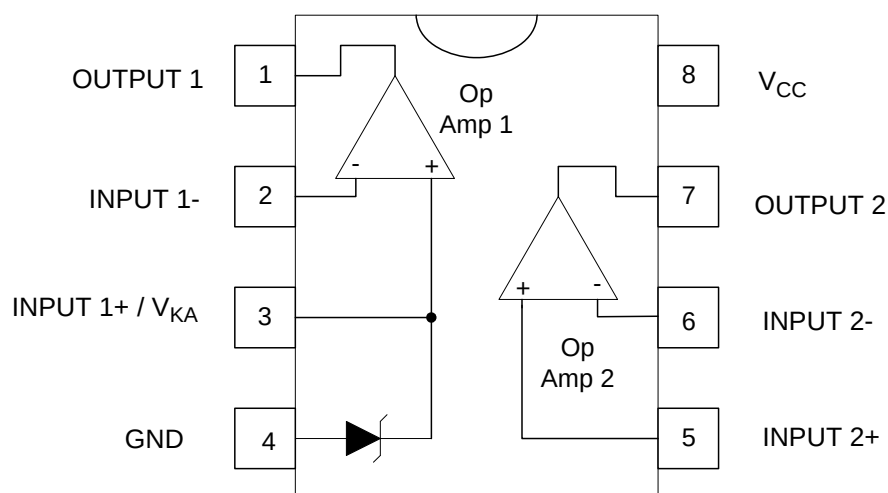
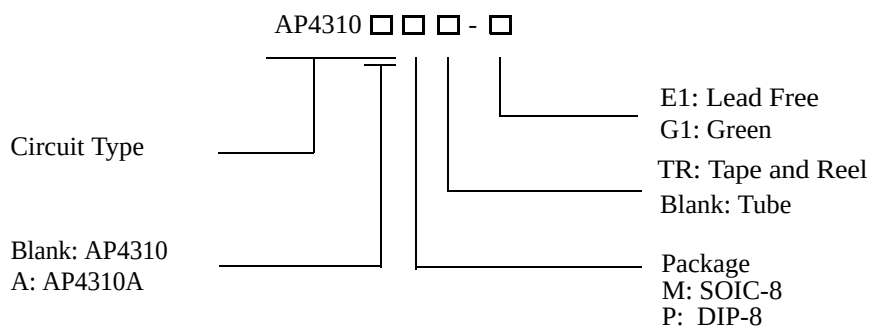


Figure 3. Functional Block Diagram of AP4310/A

**DUAL OP AMP AND VOLTAGE REFERENCE****AP4310/A****Ordering Information**

Package	Reference Voltage	Voltage Tolerance	Temperature Range	Part Number		Marking ID		Packing Type
				Lead Free	Green	Lead Free	Green	
DIP-8	2.5V	± 0.4%	-40 to105 °C	AP4310AP-E1	AP4310AP-G1	AP4310AP-E1	AP4310AP-G1	Tube
		± 1%		AP4310P-E1	AP4310P-G1	AP4310P-E1	AP4310P-G1	
SOIC-8	2.5V	± 0.4%	-40 to105 °C	AP4310AM-E1	AP4310AM-G1	AP4310AM-E1	AP4310AM-G1	Tube
				AP4310AMTR-E1	AP4310AMTR-G1	AP4310AM-E1	AP4310AM-G1	Tape & Reel
		± 1%	-40 to105 °C	AP4310M-E1	AP4310M-G1	AP4310M-E1	AP4310M-G1	Tube
				AP4310MTR-E1	AP4310MTR-G1	AP4310M-E1	AP4310M-G1	Tape & Reel

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.

**DUAL OP AMP AND VOLTAGE REFERENCE****AP4310/A****Absolute Maximum Ratings (Note 1)**

Parameter	Symbol	Value		Unit
Power Supply Voltage (V_{CC} to GND)	V_{CC}	40		V
Op Amp 1 and 2 Input Voltage Range (Pins 2, 5, 6)	V_{IN}	-0.3 to $V_{CC}+0.3$		V
Op Amp 2 Input Differential Voltage (Pins 5, 6)	V_{ID}	40		V
Voltage Reference Cathode Current (Pin 3)	I_K	100		mA
Power Dissipation ($T_A=25^{\circ}\text{C}$)	P_D	DIP-8	800	mW
		SOIC-8	500	
Operating Junction Temperature	T_J	150		$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to 150		$^{\circ}\text{C}$
Lead Temperature (Soldering 10s)	T_{LEAD}	260		$^{\circ}\text{C}$

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Min	Max	Unit
Supply Voltage	3	36	V
Ambient Temperature	-40	105	$^{\circ}\text{C}$



DUAL OP AMP AND VOLTAGE REFERENCE

AP4310/A

Electrical Characteristics

Operating Conditions: $V_{CC} = +5V$, $T_A = 25^{\circ}C$ unless otherwise specified.

Parameter		Conditions		Min	Typ	Max	Unit
Total Supply Current, excluding Current in Voltage Reference		V _{CC} =5V, no load, -40°C≤T _A ≤105°C			0.15	0.25	mA
		V _{CC} =30V, no load, -40°C≤T _A ≤105°C			0.20	0.30	
Voltage Reference Section							
Reference Voltage	AP4310A	I _K =10mA	T _A =25°C	2.49	2.50	2.51	V
			-40°C≤T _A ≤105°C	2.48	2.50	2.52	
	AP4310		T _A =25°C	2.475	2.50	2.525	V
			-40°C≤T _A ≤105°C	2.45	2.50	2.55	
Reference Voltage Deviation Over Full Temperature Range		I _K =10mA, T _A =-40 to 105°C			5	24	mV
Minimum Cathode Current for Regulation					0.01	0.05	mA
Dynamic Impedance		I _K =1.0 to 80mA, f<1kHz			0.2	0.5	Ω
Op Amp 1 Section (V _{CC} =5V, V _O =1.4V, T _A =25°C, unless otherwise noted)							
Input Offset Voltage		T _A =25°C			0.5	3	mV
		T _A =-40 to 105°C				5	
Input Offset Voltage Temperature Drift		T _A =-40 to 105°C			7		μV/°C
Input Bias Current (Inverting Input Only)		T _A =25°C			20	150	nA
Large Signal Voltage Gain		V _{CC} =15V, R _L =2kΩ, V _O =1.4 to 11.4V		85	100		dB
Power Supply Rejection Ratio		V _{CC} =5 to 30V		70	90		dB
Output Current	Source	V _{CC} =15V, V _{ID} =1V, V _O =2V		20	40		mA
	Sink	V _{CC} =15V, V _{ID} =-1V, V _O =2V		7	20		mA
Output Voltage Swing (High)		V _{CC} =30V, R _L =10kΩ, V _{ID} =1V		27	28		V
Output Voltage Swing (Low)		V _{CC} =30V, R _L =10kΩ, V _{ID} =-1V			17	100	mV
Slew Rate		V _{CC} =18V, R _L =2kΩ, A _V =1, V _{IN} =0.5 to 2V, C _L =100pF		0.2	0.5		V/μ s
Unity Gain Bandwidth		V _{CC} =30V, R _L =2kΩ, C _L =100pF		0.7	1.0		MHz

**DUAL OP AMP AND VOLTAGE REFERENCE****AP4310/A****Electrical Characteristics (Continued)**Operating Conditions: $V_{CC}=+5V$, $T_A=25^{\circ}C$ unless otherwise specified.

Parameter	Conditions	Min	Typ	Max	Unit
Op Amp 2 Section ($V_{CC}=5V$, $V_O=1.4V$, $T_A=25^{\circ}C$, unless otherwise noted)					
Input Offset Voltage	$T_A=25^{\circ}C$		0.5	3	mV
	$T_A=-40$ to $105^{\circ}C$			5	
Input Offset Voltage Temperature Drift	$T_A=-40$ to $105^{\circ}C$		7		$\mu V/^{\circ}C$
Input Offset Current	$T_A=25^{\circ}C$		2	30	nA
Input Bias Current	$T_A=25^{\circ}C$		20	150	nA
Input Voltage Range	$V_{CC}=0$ to $36V$	0		$V_{CC}-1.5$	V
Common Mode Rejection Ratio	$T_A=25^{\circ}C$, $V_{CM}=0$ to $3.5V$	70	85		dB
Large Signal Voltage Gain	$V_{CC}=15V$, $R_L=2k\Omega$, $V_O=1.4$ to $11.4V$	85	100		dB
Power Supply Rejection Ratio	$V_{CC}=5$ to $30V$	70	90		dB
Output Current	Source	$V_{CC}=15V$, $V_{ID}=1V$, $V_O=2V$	20	40	mA
	Sink	$V_{CC}=15V$, $V_{ID}=-1V$, $V_O=2V$	7	20	mA
Output Voltage Swing (High)	$V_{CC}=30V$, $R_L=10k\Omega$, $V_{ID}=1V$	27	28		V
Output Voltage Swing (Low)	$V_{CC}=30V$, $R_L=10k\Omega$, $V_{ID}=-1V$		17	100	mV
Slew Rate	$V_{CC}=18V$, $R_L=2k\Omega$, $A_V=1$, $V_{IN}=0.5$ to $2V$, $C_L=100pF$	0.2	0.5		$V/\mu s$
Unity Gain Bandwidth	$V_{CC}=30V$, $R_L=2k\Omega$, $C_L=100pF$	0.7	1.0		MHz

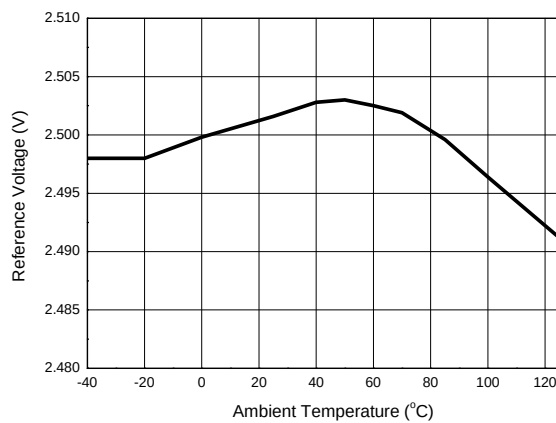
**Typical Performance Characteristics**

Figure 4. Reference Voltage vs. Ambient Temperature

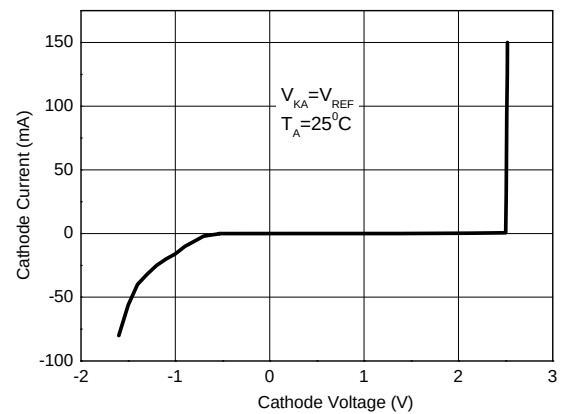


Figure 5. Cathode Current vs. Cathode Voltage

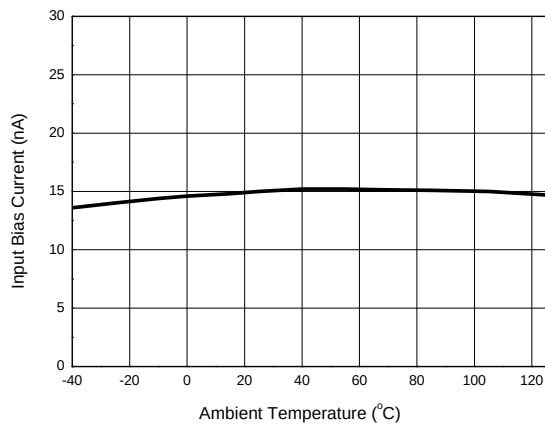


Figure 6. Input Bias Current vs. Ambient Temperature

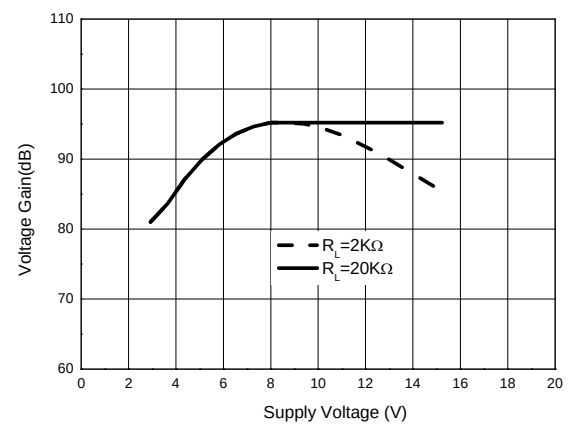


Figure 7. Op Amp Voltage Gain

Typical Application

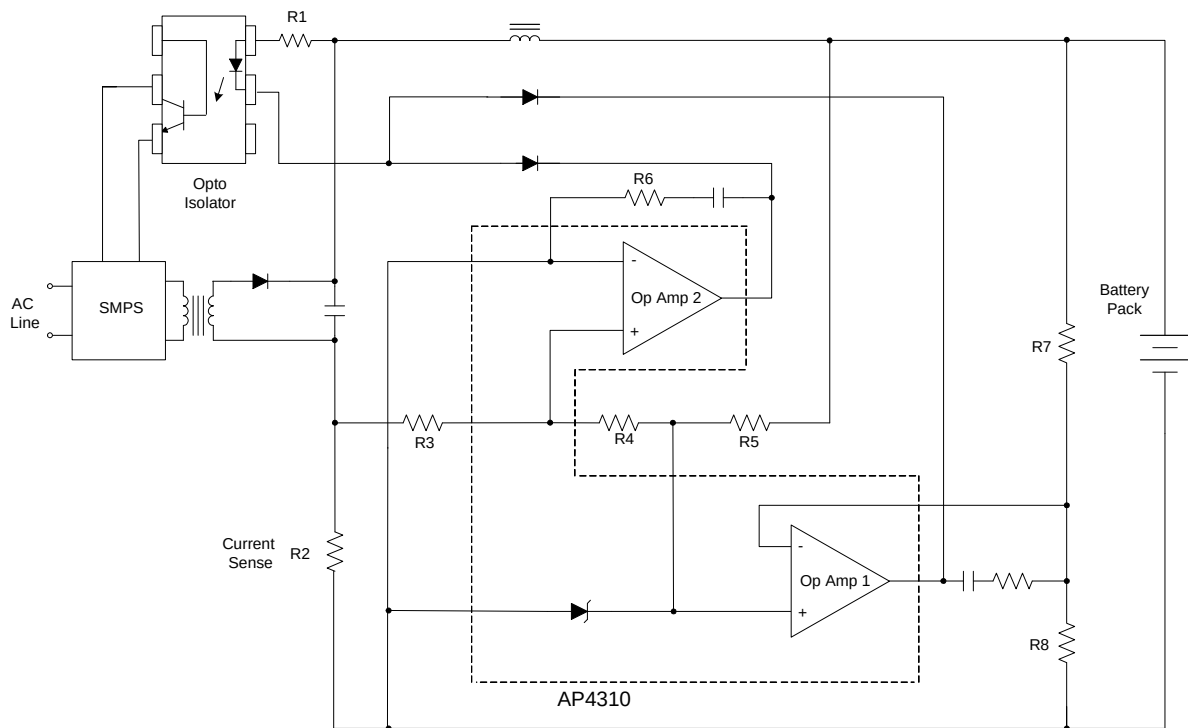
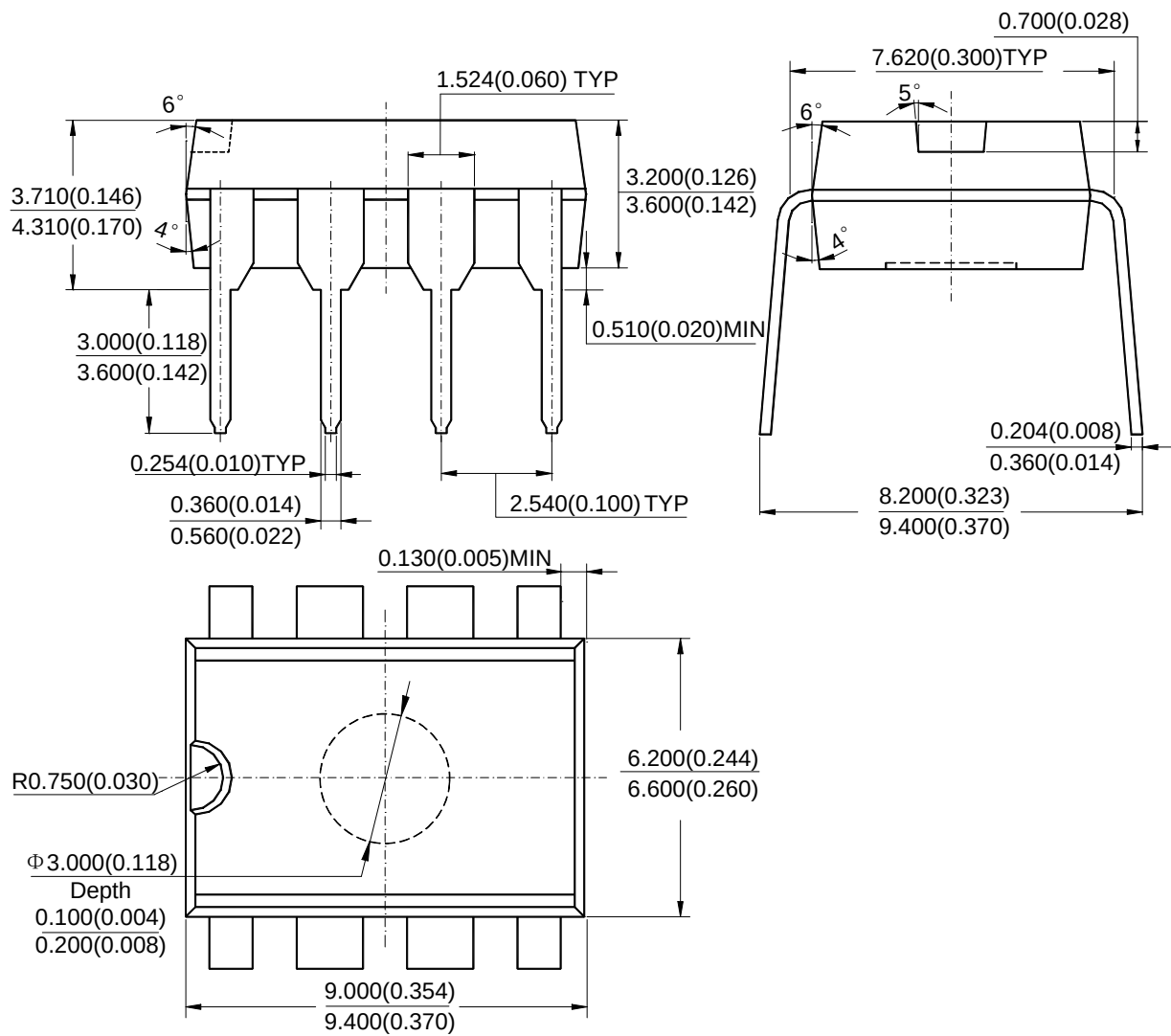
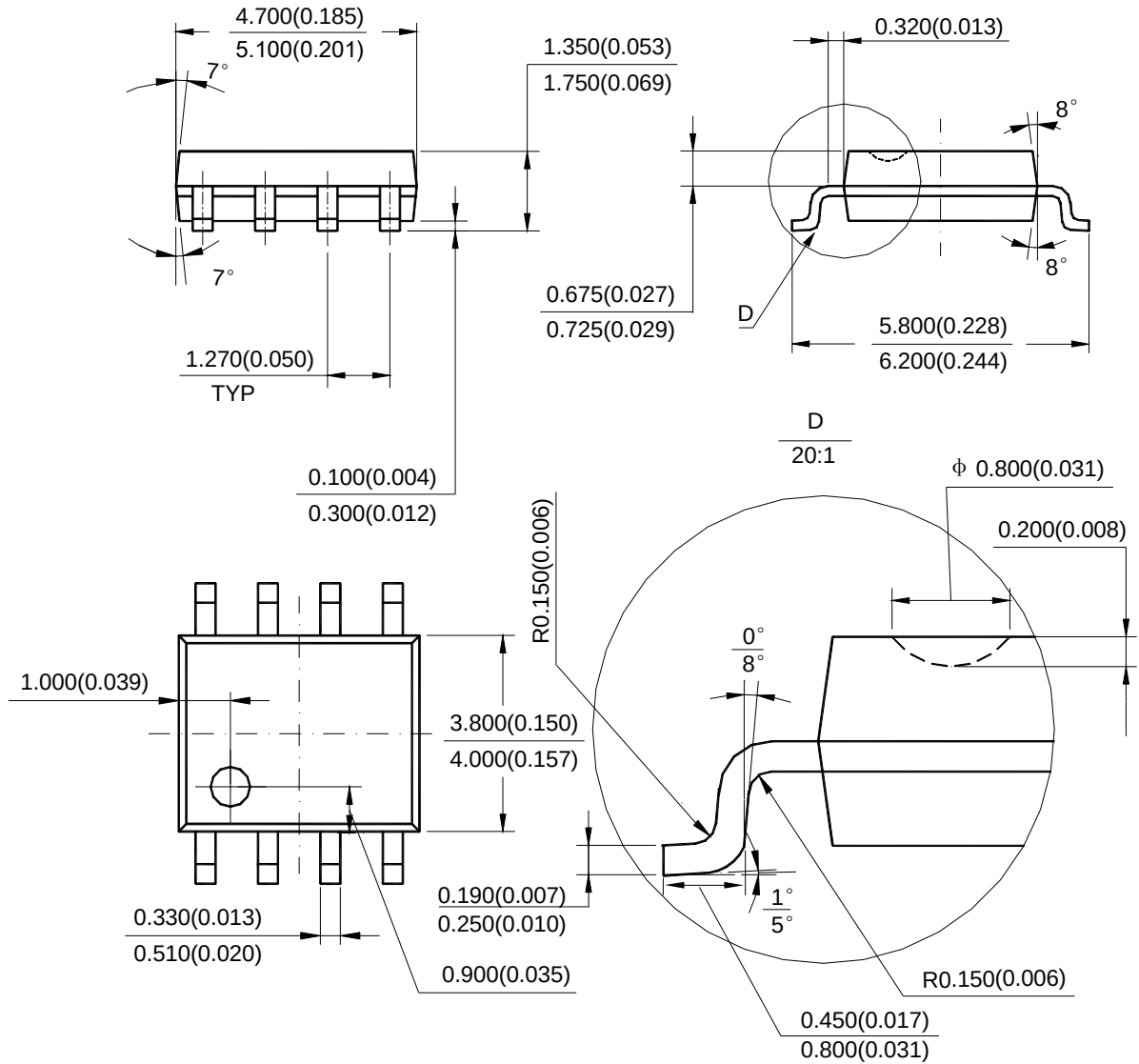


Figure 8. Application of AP4310/A in a Constant Current and Constant Voltage Charger

**DUAL OP AMP AND VOLTAGE REFERENCE****AP4310/A****Mechanical Dimensions:****DIP-8****Unit: mm(inch)**

Mechanical Dimensions (Continued):
SOIC-8
Unit: mm(inch)




BCD Semiconductor Manufacturing Limited

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MAIN SITE

- Headquarters

BCD Semiconductor Manufacturing Limited

No. 1600, Zi Xing Road, Shanghai Zizhu Science-based Industrial Park, 200241, China
Tel: +86-21-24162266, Fax: +86-21-24162277

- Wafer Fab

Shanghai SIM-BCD Semiconductor Manufacturing Co., Ltd.

800 Yi Shan Road, Shanghai 200233, China
Tel: +86-21-6485 1491, Fax: +86-21-5450 0008

REGIONAL SALES OFFICE

Shenzhen Office

Shanghai SIM-BCD Semiconductor Manufacturing Co., Ltd., Shenzhen Office
Room E, 5F, Noble Center, No.1006, 3rd Fuzhong Road, Futian District, Shenzhen, 518026, China
Tel: +86-755-8826 7951
Fax: +86-755-8826 7865

Taiwan Office

BCD Semiconductor (Taiwan) Company Limited
4F, 298-1, Rui Guang Road, Nei-Hu District, Taipei, Taiwan
Tel: +886-2-2656 2808
Fax: +886-2-2656 2806

USA Office

BCD Semiconductor Corp.
30920 Huntwood Ave. Hayward, CA 94544, USA
Tel : +1-510-324-2988
Fax: +1-510-324-2788